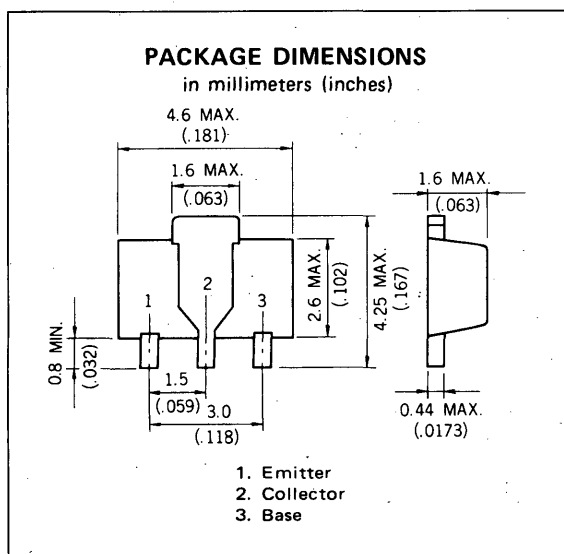


NPN SILICON EPITAXIAL TRANSISTOR
POWER MINI MOLD

DESCRIPTION

The 2SD1000 is designed for audio frequency power amplifier application, especially in Hybrid Integrated Circuits.



FEATURES

- World Standard Miniature Package
: SOT-89
- Low Collector Saturation Voltage
: $V_{CE(sat)} < 0.4 \text{ V}$ ($I_C = 500 \text{ mA}$, $I_B = 50 \text{ mA}$)
- Complements to PNP type 2SB799

ABSOLUTE MAXIMUM RATINGS (Ta = 25 °C)

Maximum Voltages and Currents

Collector to Base Voltage	V_{CBO}	60	V
Collector to Emitter Voltage	V_{CEO}	50	V
Emitter to Base Voltage	V_{EBO}	5.0	V
Collector Current (DC)	I_C	0.7	A
Collector Current (Pulse)*	I_C	1.0	A

Maximum Power Dissipation

Total Power Dissipation at 25 °C Ambient Temperature**	P_T	2.0	W
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Maximum Temperatures

Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55 to +150	°C

*PW ≤ 10 ms, duty cycle ≤ 50 %

**When mounted on ceramic substrate of 16 cm² x 0.7 mm

ELECTRICAL CHARACTERISTICS (Ta = 25 °C)

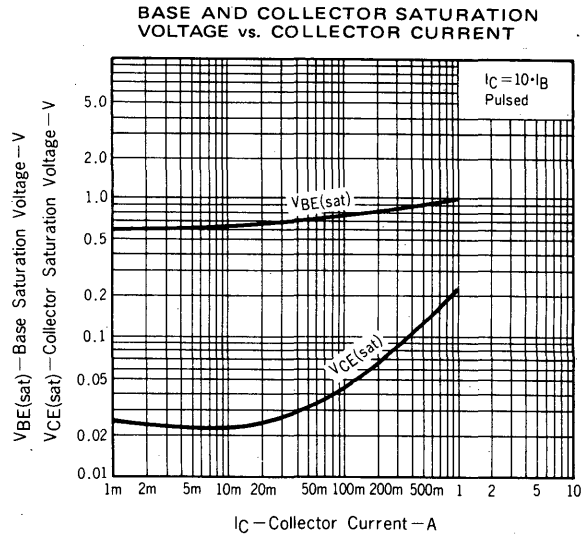
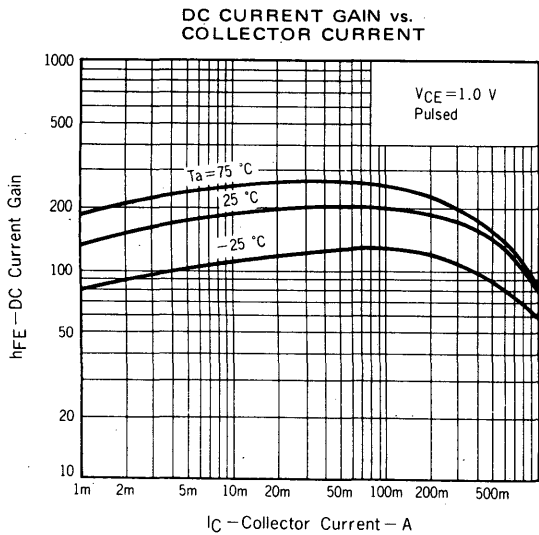
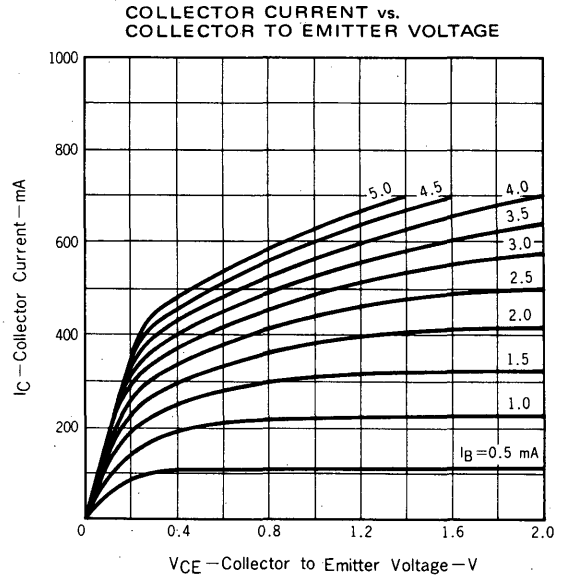
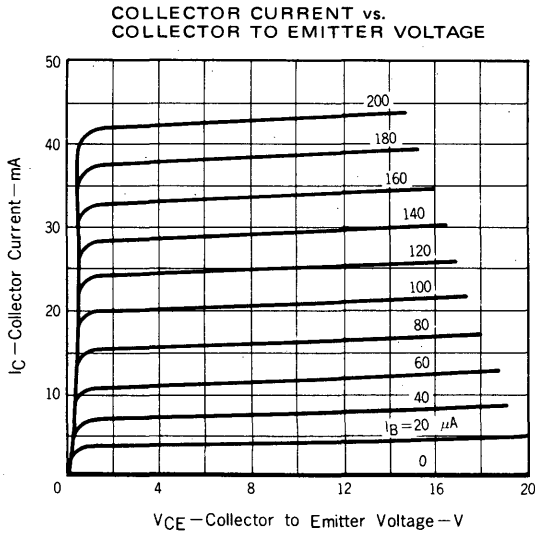
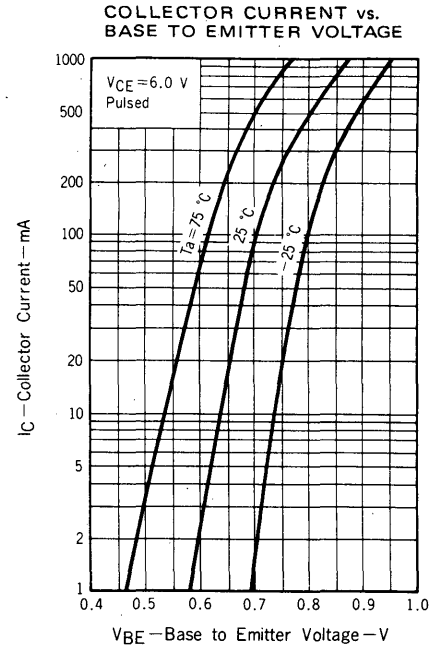
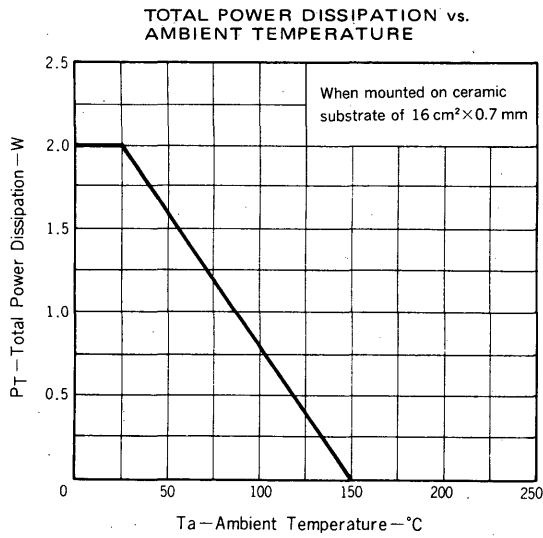
CHARACTERISTIC	SYMBOL	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
Collector Cutoff Current	I_{CBO}			100	nA	$V_{CB} = 60 \text{ V}$, $I_E = 0$
Emitter Cutoff Current	I_{EBO}			100	nA	$V_{EB} = 5.0 \text{ V}$, $I_C = 0$
DC Current Gain	h_{FE1}	90	200	400		$V_{CE} = 1.0 \text{ V}$, $I_C = 100 \text{ mA}$ ***
DC Current Gain	h_{FE2}	50	150			$V_{CE} = 1.0 \text{ V}$, $I_C = 500 \text{ mA}$ ***
Collector Saturation Voltage	$V_{CE(sat)}$		0.12	0.40	V	$I_C = 500 \text{ mA}$, $I_B = 50 \text{ mA}$ ***
Base Saturation Voltage	$V_{BE(sat)}$		0.9	1.2	V	$I_C = 500 \text{ mA}$, $I_B = 50 \text{ mA}$ ***
Base to Emitter Voltage	V_{BE}	600	635	700	mV	$V_{CE} = 6.0 \text{ V}$, $I_C = 10 \text{ mA}$ ***
Gain Bandwidth Product	f_T		110		MHz	$V_{CE} = 6.0 \text{ V}$, $I_E = -10 \text{ mA}$
Output Capacitance	C_{ob}		13		pF	$V_{CB} = 6.0 \text{ V}$, $I_E = 0$, $f = 1.0 \text{ MHz}$

***Pulsed: PW ≤ 350 μs, duty cycle ≤ 2 %

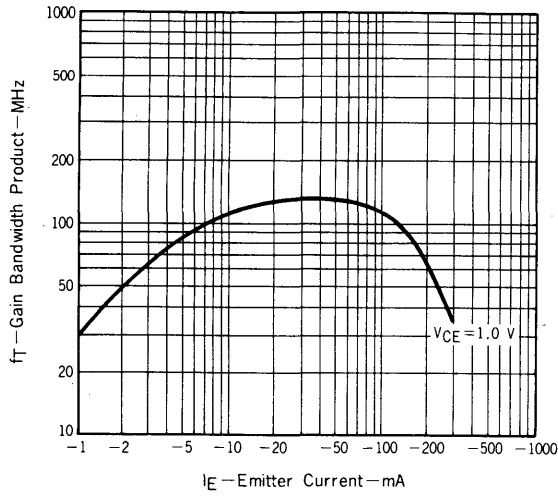
h_{FE} Classification

MARKING	LM	LL	LK
h_{FE1}	90 - 180	135 - 270	200 - 400

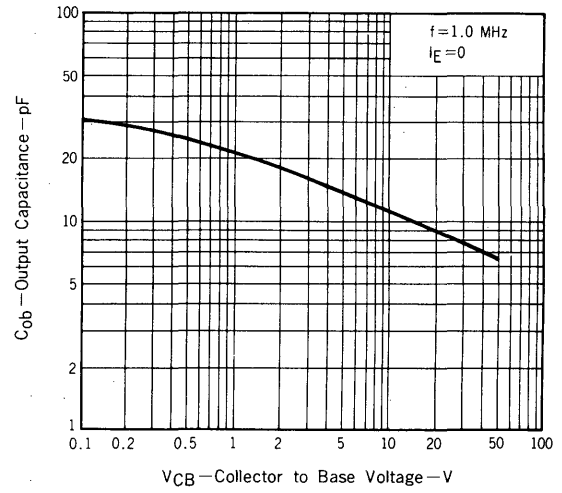
TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)



GAIN BANDWIDTH PRODUCT vs. EMITTER CURRENT



OUTPUT CAPACITANCE vs. REVERSE VOLTAGE



REFERENCE

Document Name	Document No.
NEC semiconductor device reliability/quality control system.	TEI-1202
Quality grade on NEC semiconductor devices.	IEI-1209
Semiconductor device mounting technology manual.	IEI-1207
Semiconductor device package manual.	IEI-1213
Guide to quality assurance for semiconductor devices.	MEI-1202
Semiconductor selection guide.	MF-1134

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